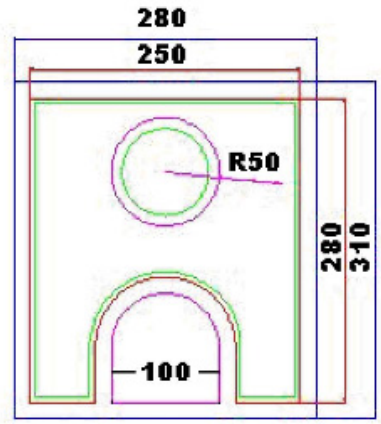
ROITHNER LASERTECHNIK GmbH
WIEDNER HAUPTSTRASSE 76 1040 VIENNA AUSTRIA
TEL. +43 1 586 52 43 -0, FAX. -44 OFFICE@ROITHNER-LASER.COM

v 1.0 01.06.2016

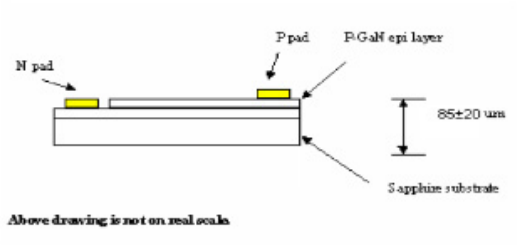
ELC-470-34

Radiation	Type	Electrodes
blue	GaN / sapphire	P + N up



Description

- Sustrate: Sapphire, epitaxial layer: GaN based material
- N bonding pad electrode: Au alloy
- P bonding pad electrode: Au alloy



Maximum Ratings

T_{amb}= 25°C, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward current (DC)		I_F			20	mA
Peak forward current	$t_p \leq 50$ µs, $t_p/T=½$	I_{FM}			100	mA

Optical and Electrical Characteristics

T_{amb}= 25°C, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	I_F=20 mA	V_F		3.3	3.5	V
Reverse current	V_R=5 V	I_R			1	µA
Dominant wavelength	I_F=20 mA	λ_p	467	470	473	nm
Full width at half maximum	I_F=20 mA	$\Delta\lambda$		30		nm
Luminous intensity	I_F=20 mA	I_v	260	280	300	mcd

Packing

Chips on adhesive film with wire-bond side top

RoHS COMPLIANT Pb Pb-Free